

Investigation Of An Alternative Path For SRF Cavity Fabrication And Surface

Processing

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Abstract

The preparation of SRF cavities includes a lengthy, costly, and safety issued electrochemical polishing (EP or BCP) step to remove the damaged layer coming from the cavity fabrication. We have shown that most of the damage layer is originated from the rolling process during the preparation of the sheet material, while subsequent deep drawing tends to leave only µm thick damage layer. We propose a 2-steps mechanical process that allows us to easily get rid of the thick damage layer on the sheets before cavity forming. The process has been established on samples and extended to large disks ready for 1.3 GHz half-cell forming and subsequent surface and material analysis before proceeding to half-cell welding. Former studies on the sample demonstrated that damages induced by forming can successfully be removed by recrystallization and less than 10 µm final chemistry.







quality

Conclusion and Perspectives

- 2 steps metallographic polishing recipe has been developed compatible with SRF applications (at IJCLab)
- Surface characterizations show smooth, non-polluted, and minor crystallographic defects
- Polishing procedure extented to the large sheets (at LAM PLAN)
- Alternative cavity forming technique has been applied to samples polished by different techniques (metallographic, chemical, mechanical)
- Increased roughness due to creation of the new grain boundaries
- Evaluated the damages of the surface (face)

To be done in 2021:

- Perform the EBSD analysis of the cross-sections (evaluate thickness of damaged layer) : June-July 2021
- Apply the heat treatment at medium temperatures (recrystallisation)
- Forming of 1.3 GHz half-cells with the following cavity fabrication using the polished disks (KEK FJPPL program)







William Magnin (LAM PLAN) for assistance with lapping and polishing work.

Part of this work was supported by the European Nuclear Science and Applications Research-2 (ENSAR-2) under grant agreement

